

MARKED-UP VERSION OF AMENDED CLAIM

1. A semiconductor structure comprising:
 - a substrate;
 - two or more adjacent conductors, disposed in at least one dielectric layer formed over said substrate and electrically isolated from each other, wherein each pair of adjacent conductors is separated by a gap; and
 - a first high dielectric constant material [formed in]
filling the gap between two adjacent conductors.

NEW VERSION OF CLAIM WITH INCORPORATED AMENDMENTS

1. A semiconductor structure comprising:
 - a substrate;
 - two or more adjacent conductors, disposed in at least one dielectric layer formed over said substrate and electrically isolated from each other, wherein each pair of adjacent conductors is separated by a gap; and
 - a first high dielectric constant material filling the gap between two adjacent conductors.